

<b>Notice of References Cited</b>	Application/Control No. 10/639,465		Applicant(s)/Patent Under Reexamination YAMAZAKI ET AL.	
	Examiner George A. Goudreau		Art Unit 1792	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,132,806	10-2000	Dutartre, Didier	427/255.18
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	"High-resolution reactive ion etching and damage effects in the silicon/ germanium silicon system"; Journal of Vacuum Science & Technology: B; (1993'); 11 (6); pp. 2224-2228; Cheung et. al.
	V	"Reactive ion etching of Si/SiGe in CF4/Ar and Cl2/BCl3/Ar discharges"; Materials Chemistry and Physics; (1999'); 60 (1); Chang et. al.; pp. 22-27
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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